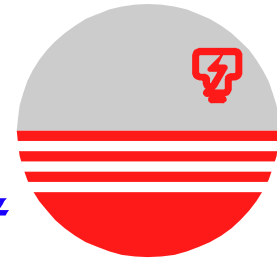


Name:  
Student ID Number:  
Section: 01/02/03/04/05 A/B  
Lecturer: Dr Jamaludin / Dr Azni Wati  
/ Dr Fazrena Azlee

**UNIVERSITI  
TENAGA  
NASIONAL**



**College of Engineering**  
Department of Electronics and Communication Engineering

**Test 2**

**SEMESTER 1, ACADEMIC YEAR 2012/2013**

Subject Code : **EEEEB273**  
Course Title : **Electronics Analysis & Design II**  
Date : **3 August 2012**  
Time Allowed : **1.5 hours**

**Instructions to the candidates:**

1. Write your Name and Student ID number. Circle your section number.
2. **Write all your answers using pen. DO NOT USE PENCIL** except for the diagram.
3. **ANSWER ALL QUESTIONS.**
4. **WRITE YOUR ANSWER ON THIS QUESTION PAPER.**
5. For BJT, use  $V_T = 26 \text{ mV}$  where appropriate.
6. Use at least **4 significant numbers** in all calculations.

**NOTE: DO NOT OPEN THE QUESTION PAPER UNTIL INSTRUCTED TO DO SO.**

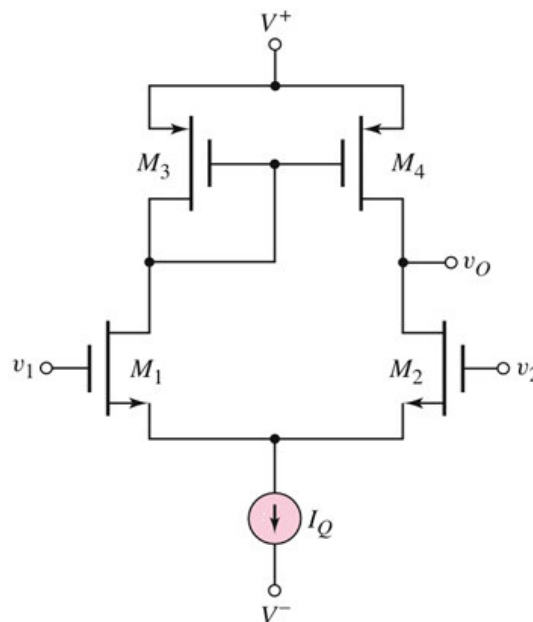
☺ **GOOD LUCK!** ☺

Question No.	1	2	3	Total
Marks				

**Question 1** [40 marks]

The circuit parameters for the differential amplifier shown in **Figure 1** are  $V^+ = 5\text{ V}$ ,  $V^- = -5\text{ V}$ ,  $A_{cm} = -0.28$ , and  $I_Q = 240\text{ }\mu\text{A}$ . The NMOS transistor parameters are  $V_{TN} = 0.4\text{ V}$ ,  $k'_n = 100\text{ }\mu\text{A/V}^2$ ,  $(W/L)_n = 8$ , and  $\lambda_n = 0.018\text{ V}^{-1}$ . The PMOS transistor parameters are  $V_{TP} = -0.4\text{ V}$ ,  $k'_p = 40\text{ }\mu\text{A/V}^2$ ,  $(W/L)_p = 10$ , and  $\lambda_p = 0.02\text{ V}^{-1}$ .

- Determine** the maximum **common-mode voltage input**,  $v_{cm}(\text{max})$ , that can be applied such that the transistors are **still biased in saturation region**. [6 marks]
- Draw the ac equivalent circuit** for the differential-mode input ( $v_1 = +v_d/2$  and  $v_2 = -v_d/2$ ). **Indicate** the resultant ac currents in all transistors. [6 marks]
- Determine** the output resistance  $R_o$  of the differential amplifier. [5 marks]
- Calculate** the small-signal differential-mode voltage gain  $A_d = v_o/v_d$ . [5 marks]
- Suggest** one way **to increase** the differential-mode voltage gain and **show** your new circuit and **justify** the change(s). [6 marks]
- Find** the **one-sided output voltage** ( $v_o$ ) taken at  $v_{D2}$  of the differential amplifier when  $v_1 = (0.10 + 0.05 \sin \omega t)\text{ mV}$  and  $v_2 = (-0.10 + 0.05 \sin \omega t)\text{ mV}$ . [12 marks]

**Figure 1**

**Answers for Question 1**

$$(a) \quad V_{SG3} = [\sqrt{I_{D3}/K_n}] - V_{TP}$$

$$= [\sqrt{I_Q/2}/[(k'_p/2)(W/L)_p]] - V_{TP} \quad (3)$$

$$= [\sqrt{(120\mu)/[(40\mu/2)(10)]}] + 0.4$$

$$= 1.175 \text{ V}$$

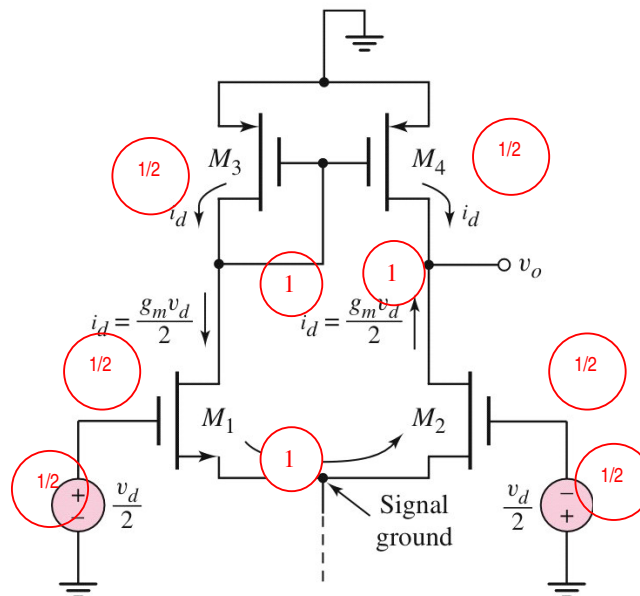
$$v_{cm(max)} = V^+ - V_{SG3} - V_{DS1(sat)} + V_{GS1}$$

$$= V^+ - V_{SG3} - (V_{GS1} - V_{TN}) + V_{GS1} = V^+ - V_{SG3} + V_{TN} \quad (3)$$

$$= 5 - 1.175 + 0.4$$

$$= 4.225 \text{ V}$$

(b)



**Answers for Question 1 (Cont.)**

(c)

$$r_{o2} = 1/(\lambda_n I_D) = [(0.018)(120\mu)]^{-1} = 463 \text{ k}\Omega \quad (2)$$

$$r_{o4} = 1/(\lambda_p I_D) = [(0.02)(120\mu)]^{-1} = 416.7 \text{ k}\Omega \quad (2)$$

$$R_o = r_{o2} // r_{o4} = 219.3 \text{ k}\Omega \quad (1)$$

(d)

$$R_o = r_{o2} // r_{o4} = 219.3 \text{ k}\Omega \quad (1)$$

$$g_m = 2\sqrt{[K_n I_D]} = 2\sqrt{[(k'_n/2)(W/L)_n(I_Q/2)]} \quad (2)$$

$$= 2\sqrt{[(100\mu/2)(8)(120\mu)]} = 0.4382 \text{ mA/V}^2$$

$$A_d = g_m R_o = (0.4382\text{m})(219.3\text{k}) = 96.09 \quad (2)$$

(e)

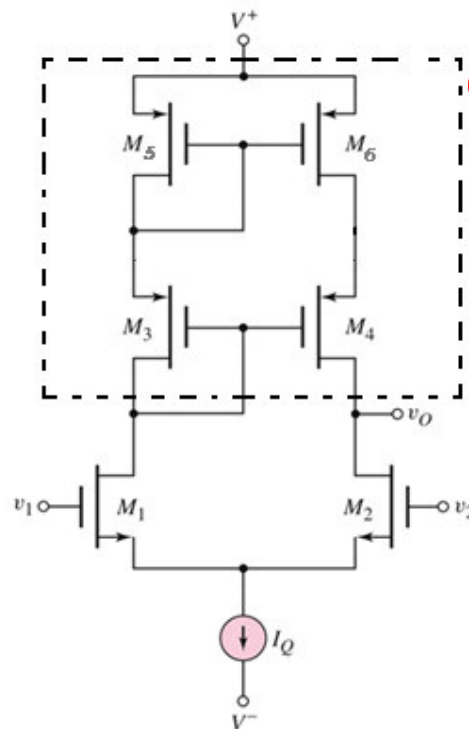
**Increase voltage gain by using cascode active load.** (2)

$$A_d = g_m R_o \quad (1)$$

Previous  $R_o = r_{o2} // r_{o4}$

New circuit  $R_o = r_{o2} // R_o(\text{active load}) = r_{o2} // g_m r_{o4} r_{o6} \approx r_{o2}$  (1)

The new  $R_o$  is larger than the previous one.



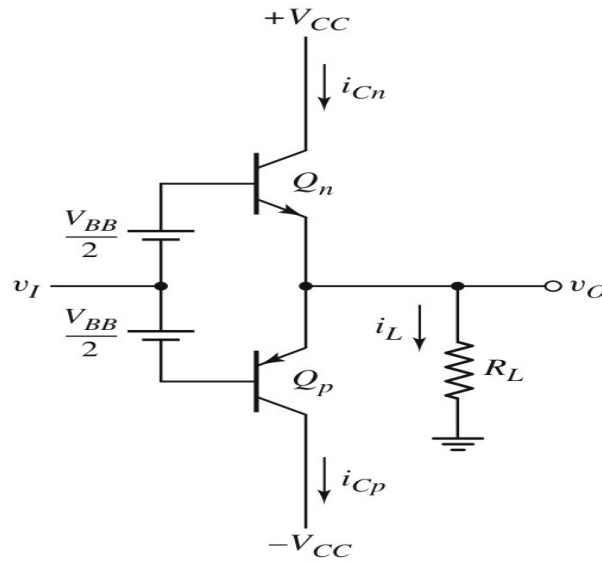
(2)

-transistor type PMOS  
-within cascode connections  
-connection with diff-amp

**Answers for Question 1 (Cont.)**

$$\begin{aligned} \text{(f)} \quad v_d &= v_1 - v_2 && (1) \\ &= (0.10 + 0.05 \sin \omega t) - (-0.10 + 0.05 \sin \omega t) && (2) \\ &= 0.20 \text{ mV} && (1) \\ v_{cm} &= (v_1 + v_2)/2 && (1) \\ &= [(0.10 + 0.05 \sin \omega t) + (-0.10 + 0.05 \sin \omega t)]/2 && (2) \\ &= 0.05 \sin \omega t \text{ mV} && (1) \\ v_O &= A_d v_d + A_{cm} v_{cm} && (2) \\ &= (96.09)(0.2 \text{ mV}) + (-0.28)(0.05 \sin \omega t \text{ mV}) && (1) \\ &= (19.22 - 0.014 \sin \omega t) \text{ mV} && (1) \end{aligned}$$

**Question 2 [30 marks]**



**Figure 3**

For a simplified class-AB output stage with BJTs in **Figure 3**, given that  $V_{CC} = 5 \text{ V}$  and  $R_L = 1 \text{ k}\Omega$ . For each transistor, the reverse-bias saturation current is  $I_S = 2 \times 10^{-15} \text{ A}$ .

- a) **What** are two **disadvantages** of class-AB output stage compared to the class-B output stage? [4 marks]
- b) **What** is the **advantage** of class-AB output stage compared to the class-B output stage? [2 marks]
- c) **Determine** the value of  $V_{BB}$  that produces  $i_{Cn} = i_{Cp} = 1.1 \text{ mA}$  when  $v_I = 0 \text{ V}$ . **What** is the power dissipated in each transistor? [6 marks]
- d) For  $v_O = -3.6 \text{ V}$ , **determine**  $i_L$ ,  $i_{Cn}$ ,  $i_{Cp}$ , and  $v_I$ . Reiterate your calculation twice for  $i_{Cn}$  and  $i_{Cp}$ . **What** is the power dissipated in  $Q_n$ ,  $Q_p$ , and  $R_L$ ? [18 marks]

**Answers for Question 2**

- a) i) Required power handling capability of  $Q$ s in class-AB will be *slightly larger* than class-B.  
 ii) **Power Conversion Efficiency ( $\eta$ )** will be *less* than class-B. [2 marks for each answer]
- b) **Eliminating crossover distortion in the class-B.** [2 marks]

**Answers for Question 2 (Cont.)**

c)

$$\begin{aligned}
 i_{Cn} &= I_S \exp(V_{BE_n} / V_T) \\
 V_{BE_n} &= V_T \ln(i_{Cn} / I_S) && [1] \\
 &= (0.026) \ln(1.1 \times 10^{-3} / 2 \times 10^{-15}) = 0.70286 \text{ V} && [0.5, 0.5] \\
 V_{BB} &= 2 V_{BE} && [1] \\
 &= 2 \times 0.70286 = 1.40572 \text{ V} && [0.5, 0.5] \\
 P_Q &= i_{Cn} v_{CE} && [1] \\
 &= (1.1 \text{ m})(5 \text{ V} - 0 \text{ V}) = 5.5 \text{ mW} && [0.5, 0.5]
 \end{aligned}$$

d)

$$\begin{aligned}
 \text{For } v_O = -3.6 \text{ V,} \quad i_L &= v_O / R_L && [1] \\
 &= (-3.6 \text{ V}) / (1 \text{ k}\Omega) = -3.6 \text{ mA} && [0.5, 0.5]
 \end{aligned}$$

$$\begin{aligned}
 \text{Approximation:} \quad i_{Cp} &\approx |i_L| = 3.6 \text{ mA} && [1] \\
 v_{EBp} &= V_T \ln(i_{Cp} / I_S) && [0.5] \\
 &= (0.026) \ln(3.6 \times 10^{-3} / 2 \times 10^{-15}) = 0.73369 \text{ V} && [0.5] \\
 v_{BE_n} &= V_{BB} - v_{EBp} && [1] \\
 &= 1.40572 - 0.73369 = 0.67203 \text{ V} && [0.5] \\
 i_{Cn} &= I_S \exp(V_{BE_n} / V_T) && [1] \\
 &= (2 \times 10^{-15}) \exp(0.67203 / 0.026) = 0.336026 \text{ mA} && [0.5]
 \end{aligned}$$

$$\begin{aligned}
 \text{Then, finally} \quad i_{Cp} &\approx i_{Cn} - i_L && [1] \\
 &= (0.336026 \text{ m}) - (-3.6 \text{ m}) = 3.936026 \text{ mA} && [0.5] \\
 v_{EBp} &= V_T \ln(i_{Cp} / I_S) && [0.5] \\
 &= (0.026) \ln(3.936026 \times 10^{-3} / 2 \times 10^{-15}) = 0.73601 \text{ V} && [0.5] \\
 v_{BE_n} &= V_{BB} - v_{EBp} && [0.5] \\
 &= 1.40572 - 0.73601 = 0.66971 \text{ V} && [0.5] \\
 i_{Cn} &= I_S \exp(V_{BE_n} / V_T) && [0.5] \\
 &= (2 \times 10^{-15}) \exp(0.66971 / 0.026) = 0.307341 \text{ mA} && [0.5] \\
 i_{Cp} &= i_{Cn} - i_L && [0.5] \\
 &= (0.307341 \text{ m}) - (-3.6 \text{ m}) = 3.907341 \text{ mA} && [0.5] \\
 v_I &= v_O - v_{EBp} + V_{BB}/2 && [1] \\
 &= (-3.6) - 0.73601 + 1.40572/2 = -3.63315 \text{ V} && [0.5]
 \end{aligned}$$

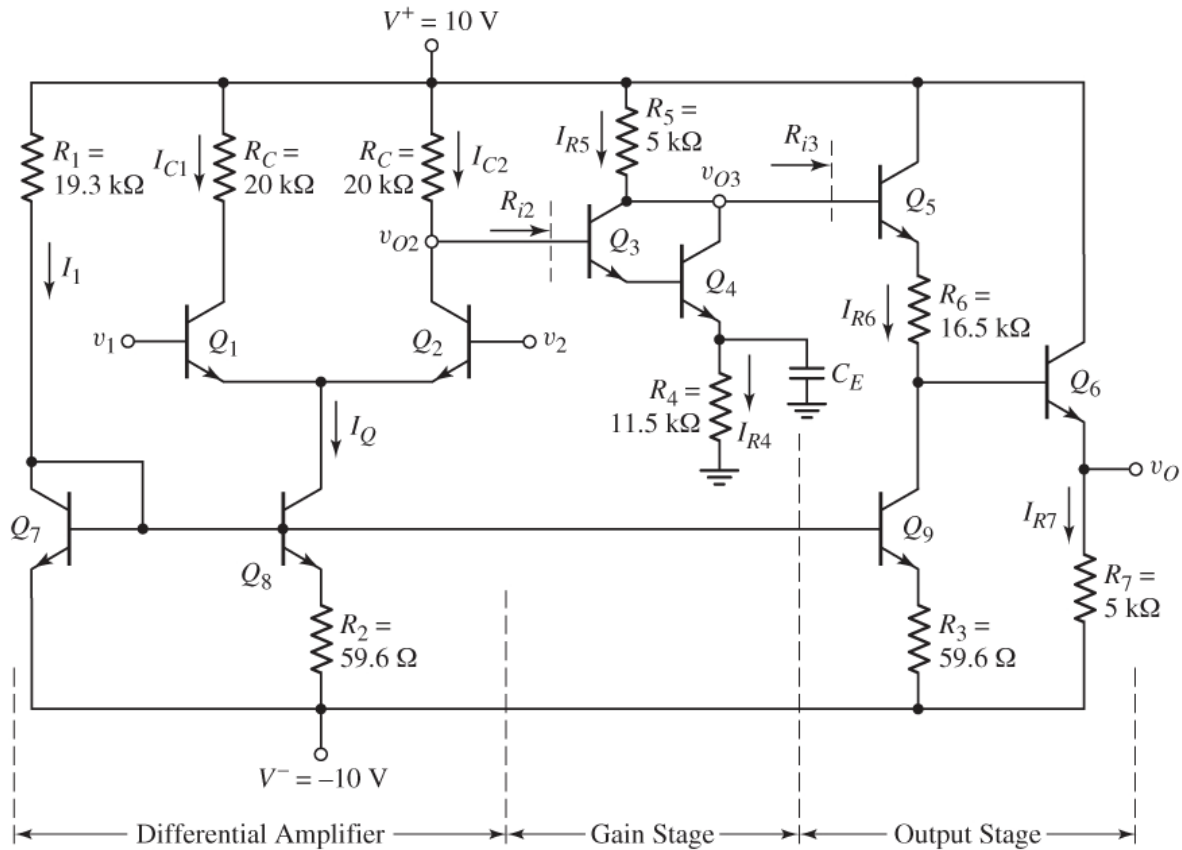
**Power:**

$$\begin{aligned}
 \text{For } Q_n: \quad P_{Qn} &= i_{Cn} v_{CE_n} && [1] \\
 &= (0.307341 \text{ m})(5 - (-3.6)) = 2.643 \text{ mW} && [0.5, 0.5]
 \end{aligned}$$

$$\begin{aligned}
 \text{For } Q_p: \quad P_{Qp} &= i_{Cp} v_{ECp} && [1] \\
 &= (3.907341 \text{ m})(-3.6 - (-5)) = 5.470 \text{ mW} && [0.5, 0.5]
 \end{aligned}$$

$$\begin{aligned}
 \text{For } R_L: \quad P_{RL} &= i_L^2 R_L && [1] \\
 &= (-3.6 \text{ mA})^2 (1 \text{ k}\Omega) = 12.96 \text{ mW} && [0.5, 0.5]
 \end{aligned}$$

**Question 3 [30 marks]**



**Figure 3**

Refer to **Figure 3**. It is given that  $I_Q = I_{R4} = I_{R6} = 0.4 \text{ mA}$ , and  $I_{R7} = 2 \text{ mA}$ . Neglect base currents and assume  $V_{BE(\text{on})} = 0.7 \text{ V}$  for all transistors except  $Q_8$  and  $Q_9$  in the **Widlar** circuit.

- a) **List all transistors and resistors forming the biasing stage of the circuit in the Figure 3?** [3 marks]
- b) **Calculate the common-mode input range. State your assumptions.** [7 marks]
- c) **Calculate overall gain of the circuit. Assume  $\beta = 100$  and  $V_A = \infty$ . It is given that the gain of the **Darlington Pair** can be calculated using** [18 marks]
 
$$A_{v2} = \left( \frac{I_{R4}}{2V_T} \right) (R_5 \parallel R_{i3})$$
- d) **Comment on the loading effect of the output stage onto the gain stage.** [2 marks]



**Answers for Question 3**

a)

 **$Q_7, R_1, Q_8, R_2, Q_9$  and  $R_3$ .****[0.5 mark each]**

b)

**$V_{cm}(\text{max}) = V_{C1}$ , assume  $V_{CE}(\text{min}) = V_{BE}(\text{on})$  [1]**

**$V_{C1} = V^+ - I_{C1} R_C = 10 - (0.2\text{m})(20\text{k}) = 6 \text{ V}$  [2]**

**$V_{cm}(\text{min}) = V^- + V_{BE1} + V_{BE8}$  [2]**

**assume neglect  $V_{R2}$  [0.5]**

**$V_{cm}(\text{min}) = -10 + 0.7 + 0.7 = -8.6 \text{ V}$  [1.5]**

c)

**$A_d = A_{d1} \cdot A_{v2} \cdot A_{v3} = \left( \frac{v_{o2}}{v_1 - v_2} \right) \cdot \left( \frac{v_{o3}}{v_{o2}} \right) \cdot \left( \frac{v_o}{v_{o3}} \right)$  [2]**

**$A_{d1} = \left( \frac{V_{o2}}{v_d} \right) = \frac{g_m}{2} (R_C \parallel R_{i2})$  [2]**

**$R_{i2} = r_{\pi3} + (1 + \beta)r_{\pi4}$  [2]**

**$r_{\pi4} = \beta V_T / I_{R4} = (100)(0.026) / 0.4\text{m} = 6.5\text{k}\Omega$  [0.5]**

**$r_{\pi3} \cong \beta^2 V_T / I_{R4} = (100)^2 (0.026) / 0.4\text{m} = 650\text{k}\Omega$  [1.5]**

**$R_{i2} = 650\text{k} + (101)(6.5\text{k}) = 1307\text{k}\Omega$  [0.5]**

**$g_m = I_Q / (2V_T) = 0.4\text{m} / (2 \times 0.026) = 7.70\text{mA/V}$  [0.5]**

**$\therefore A_{d1} = (7.70\text{m}/2)(20\text{k} \parallel 1307\text{k}) = 75.8$  [1]**

**$R_{i3} = r_{\pi5} + (1 + \beta)[R_6 + r_{\pi6} + (1 + \beta)R_7]$  [2]**

**$r_{\pi5} = \beta V_T / I_{R6} = (100)(0.026) / 0.4\text{m} = 6.5\text{k}\Omega$  [0.5]**

**$r_{\pi6} = \beta V_T / I_{R7} = (100)(0.026) / 2\text{m} = 1.3\text{k}\Omega$  [0.5]**

**$R_{i3} = 6.5\text{k} + (1 + 100)[16.5\text{k} + 1.3\text{k} + (1 + 100)5\text{k}] = 52.8\text{M}\Omega$  [1]**

**$A_{v2} = \frac{I_{R4}}{2V_T} (R_5 \parallel R_{i3}) = \frac{0.4\text{m}}{2(0.026)} (5\text{k} \parallel 52.8\text{M}) = 38.5$  [1]**

**$A_{v3} \approx 1$  [1]**

**$A_d = (75.8)(38.5)(1) = 2918$  [2]**

d)

**Since  $R_{i3} \gg R_5$ , the output stage does not load down the gain stage [2]**

## Appendix: BASIC FORMULA

### BJT

$$i_C = I_S e^{v_{BE}/V_T}; \text{npn}$$

$$i_C = I_S e^{v_{EB}/V_T}; \text{pnp}$$

$$i_C = \alpha i_E = \beta i_B$$

$$i_E = i_B + i_C$$

$$\alpha = \frac{\beta}{\beta + 1}$$

;Small signal

$$\beta = g_m r_\pi$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

### MOSFET

;N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k'_n}{2} \cdot \frac{W}{L}$$

;P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{k'_p}{2} \cdot \frac{W}{L}$$

;Small signal

$$g_m = 2K_n (V_{GSQ} - V_{TN}) = 2\sqrt{K_n I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$